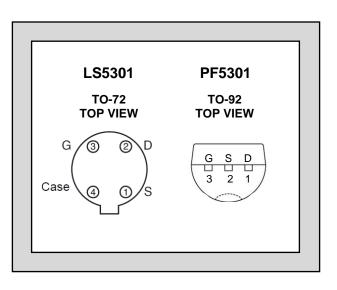
LINEAR SYSTEMS

Twenty-Five Years Of Quality Through Innovation

FEATURES					
REPLACEMENT FOR LF5301, PF5301					
HIGH INPUT INPEDANCE	$I_{G} = 0.100 \text{ pA}$				
HIGH GAIN $g_{fs} = 70 \ \mu S$					
ABSOLUTE MAXIMUM RATINGS ¹					
@ 25 °C (unless otherwise stated), TA=25°C					
Maximum Temperatures					
Storage Temperature (TO-72)	-55 to 150°C				
Storage Temperature (TO-92)	-55 to 150°C				
Maximum Power Dissipation ²					
Continuous Power Dissipation, TA=25°C	300mW				
Maximum Currents					
Gate Current	50mA				
Maximum Voltages					
Gate to Drain	-30V				
Gate to Source	-30V				

LS5301, PF5301

VERY HIGH INPUT IMPEDANCE N-CHANNEL JFET AMPLIFIER



COMMON ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC		MIN	TYP	MAX	UNIT	CONDITIONS		
BV _{GSS}	Gate to Source Breakdown Voltage		-30			V	$V_{DS} = 0V, I_D = -1\mu A$		
V _{GS(off)}	Gate to Source Cutoff Voltage		-0.6		-3.0		V _{DS} = 10V, I _D = 1nA		
lgss	Gate Leakage Current	LS5301			-1				
		PF5301			-5	pА	$V_{DS} = 0V, V_{GS} = -15V$		
lg	Gate Operating Current			-0.04			$V_{DG} = 6V, I_D = 5\mu A$		
IDSS	Drain to Source Saturation Current		30		500	μA	$V_{DS} = 10V, V_{GS} = 0V$		
g fs	Forward Transconductance		70		500	μS	$V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$		
Ciss	Input Capacitance				3	~_	V _{DS} = 10V, V _{GS} = 0V, <i>f</i> = 1MHz		
Crss	Reverse Transfer Capacitance	e			1.5	pF	$v_{DS} = 10v, v_{GS} = 0v, T = TMHZ$		
en	Equivalent Noise Voltage			45	150	nV/√Hz	$V_{DG} = 10V, I_D = 50\mu A, f = 100Hz$		

<u>NOTES</u>

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.

- 2. Derate PF series 2.8mW/° C when TA>25° C. Derate LS series 2.0mW°C when TA>25° C
- 3. All MIN/TYP/MAX limits are absolute numbers. Negative signs indicated electrical polarity only.

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Linear Integrated Systems (LIS) is a 25-year-old, third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company President John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, Co-Founder and Vice President of R&D at Intersil, and Founder/President of Micro Power Systems.

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